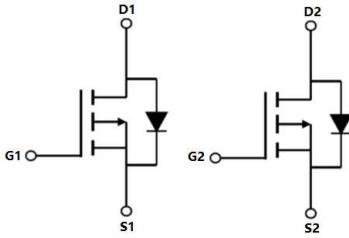


## Description

<b>Features</b> <ul style="list-style-type: none"> <li>● <math>V_{DS} = -30V</math>, <math>I_D = -5.1A</math></li> <li><math>R_{DS(ON)} &lt; 55m\Omega</math> @ <math>V_{GS} = -10V</math></li> <li><math>R_{DS(ON)} &lt; 90m\Omega</math> @ <math>V_{GS} = -4.5V</math></li> <li>● Advanced Trench Technology</li> <li>● Excellent <math>R_{DS(ON)}</math> and Low Gate Charge</li> <li>● Lead free product is acquired</li> </ul>	<b>Application</b> <ul style="list-style-type: none"> <li>● PWM Applications</li> <li>● Load Switch</li> <li>● Power Management</li> </ul>
 SOP-8	 Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM5DP03-S8	VSM5DP03	TAPING	SOP-8	13inch	4000	48000

## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
$V_{DSS}$	Drain-Source Voltage		-30	V
$V_{GSS}$	Gate-Source Voltage		$\pm 20$	V
$I_D$	Continuous Drain Current		-5.1	A
	$T_A = 100^\circ C$	-3.3	A	
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>		-20.4	A
$P_D$	Power Dissipation	$T_A = 25^\circ C$	2.15	W
$R_{Theta}$	Thermal Resistance, Junction to Ambient		58	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ C$

## Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise specified)

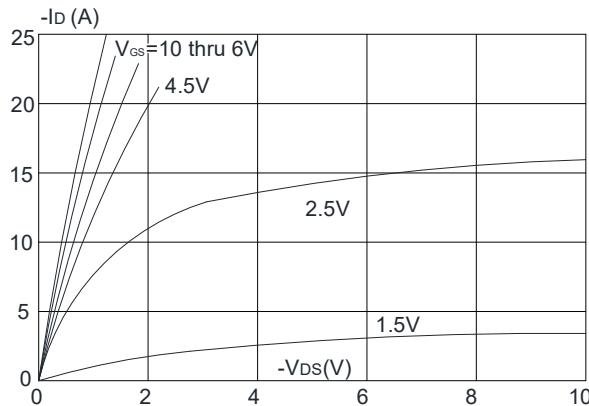
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D = -250\mu\text{A}$	-30	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}$ , $V_{GS}=0\text{V}$ ,	-	-	-1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D = -250\mu\text{A}$	-1.0	-1.6	-2.5	V
$R_{DS(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{GS} = -10\text{V}$ , $I_D = -5\text{A}$	-	43	55	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$ , $I_D = -4\text{A}$	-	66	90	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	580	-	pF
$C_{oss}$	Output Capacitance		-	98	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	74	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = -15\text{V}$ , $I_D = -5.1\text{A}$ , $V_{GS} = -10\text{V}$	-	6.8	-	nC
$Q_{gs}$	Gate-Source Charge		-	1	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.4	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15\text{V}$ , $I_D = -1\text{A}$ , $V_{GS} = -10\text{V}$ , $R_{\text{GEN}} = 2.5\Omega$	-	14	-	ns
$t_r$	Turn-on Rise Time		-	61	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	19	-	ns
$t_f$	Turn-off Fall Time		-	10	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	-5.1	A	
$I_{sM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-20.4	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_s = -5.1\text{A}$	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

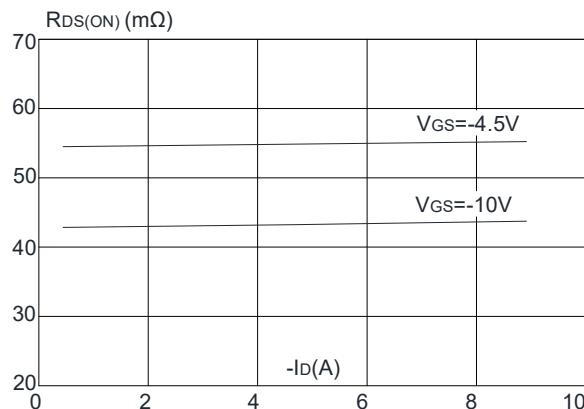
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 2\%$

## Typical Performance Characteristics

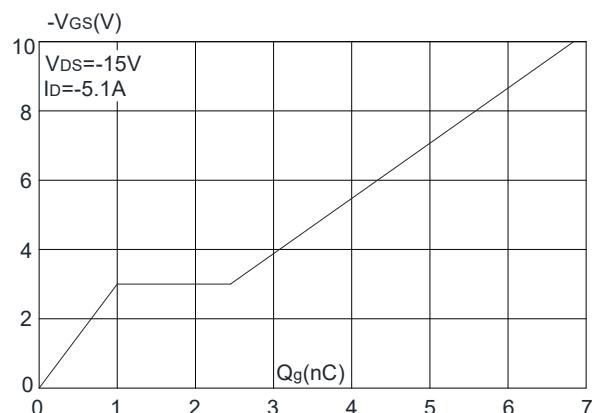
**Figure 1:** Output Characteristics



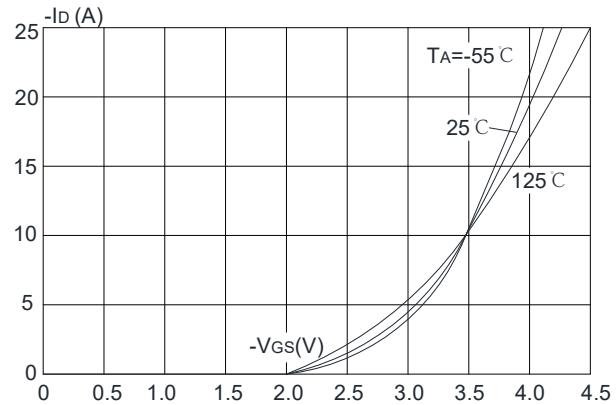
**Figure 3:** On-resistance vs. Drain Current



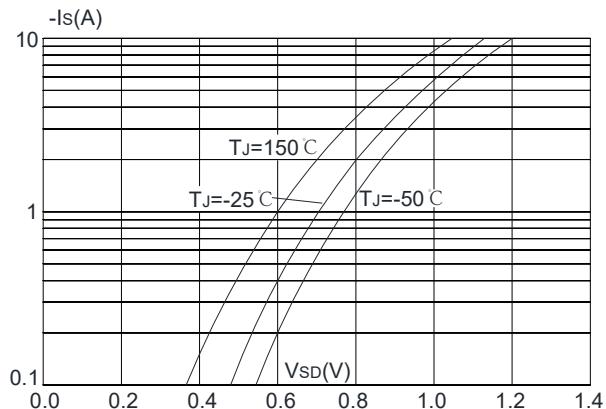
**Figure 5:** Gate Charge Characteristics



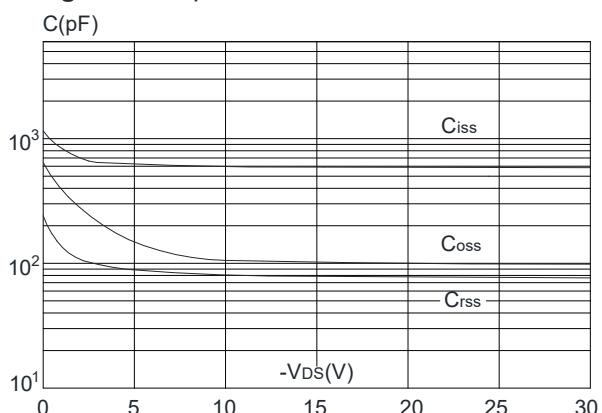
**Figure 2:** Typical Transfer Characteristics



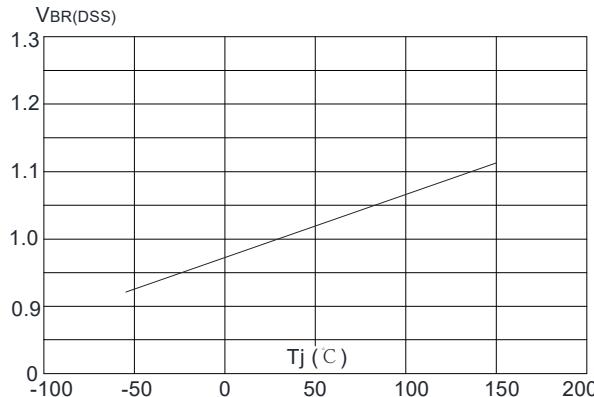
**Figure 4:** Body Diode Characteristics



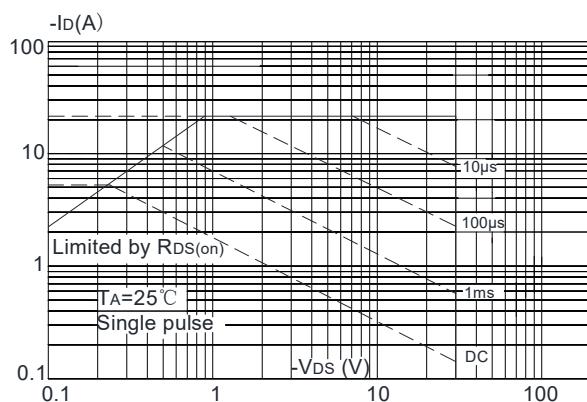
**Figure 6:** Capacitance Characteristics



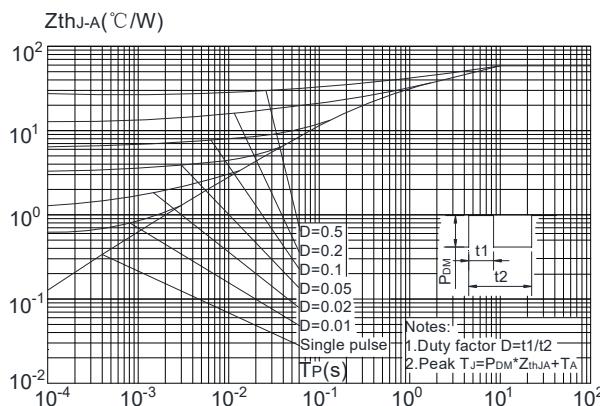
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



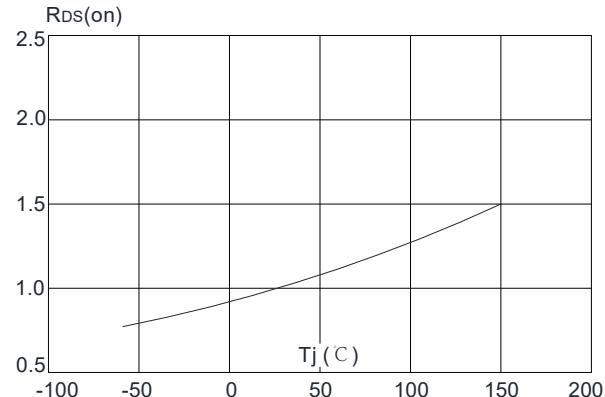
**Figure 9:** Maximum Safe Operating Area



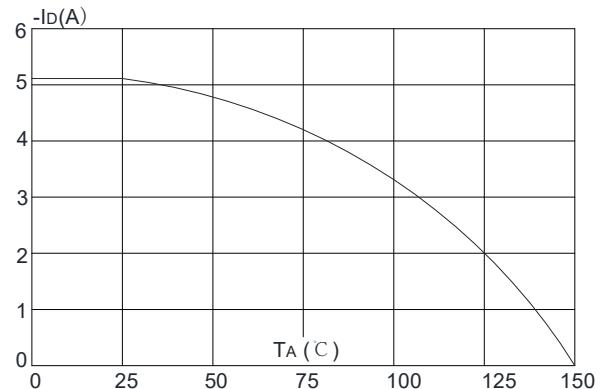
**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Figure 8:** Normalized on Resistance vs. Junction Temperature

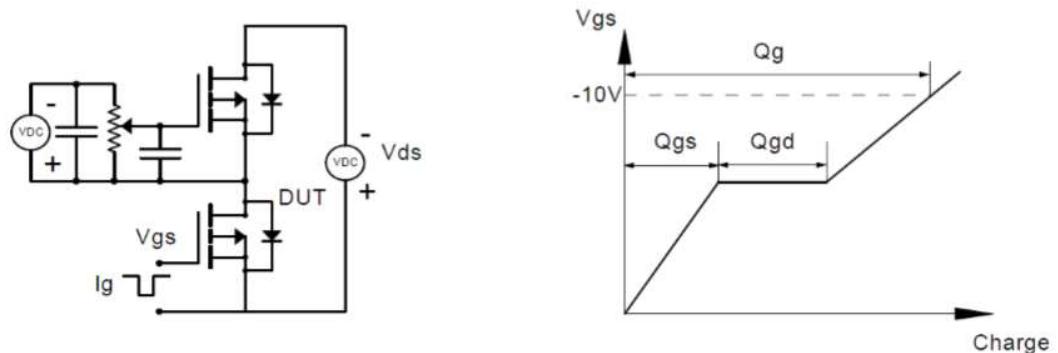


**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

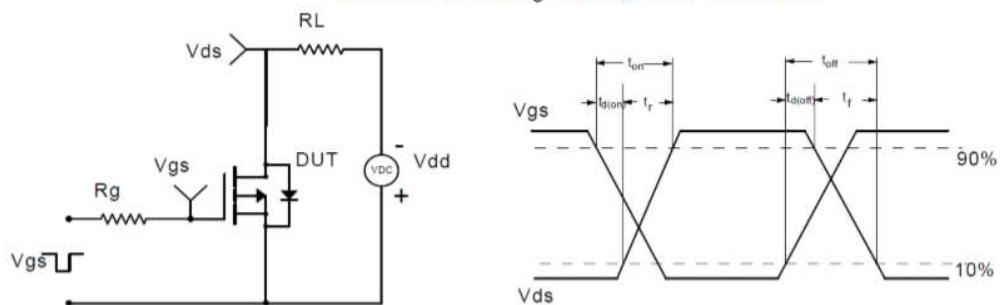


## Test Circuit

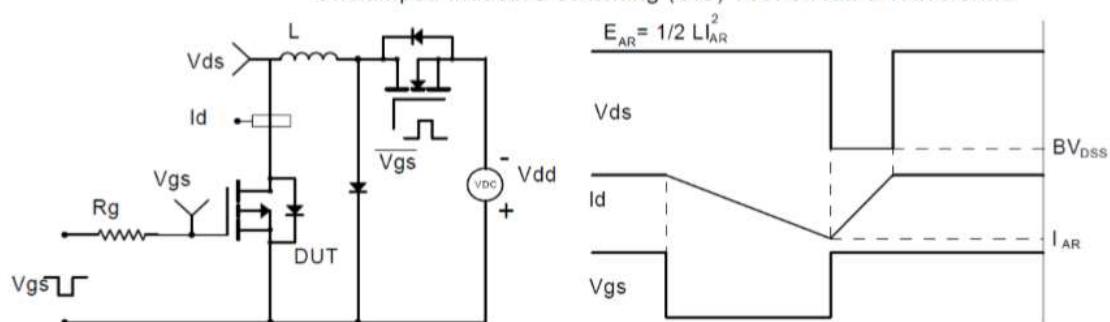
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

